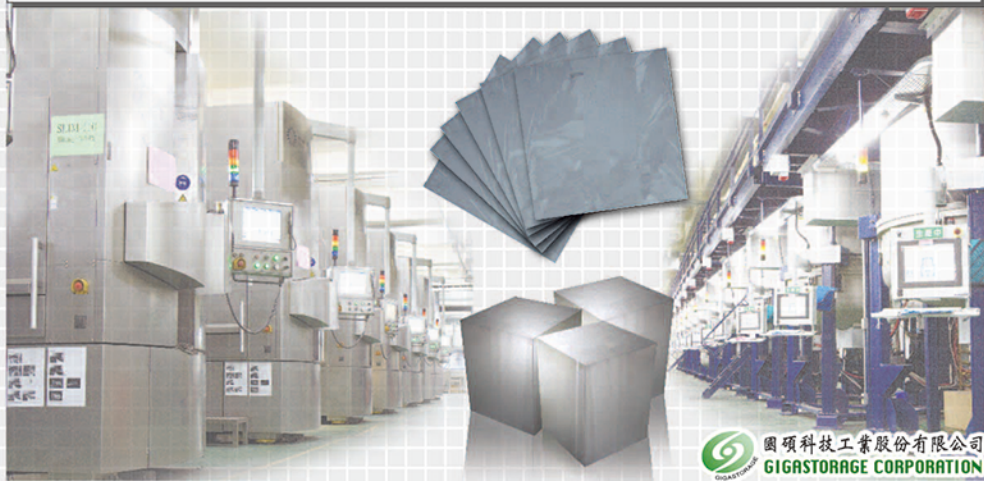




GIGASTORAGE

Quality . Technology . Innovation . Service



國碩科技工業股份有限公司
GIGASTORAGE CORPORATION

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Multi-crystalline Silicon Wafer Specification Sheet

Material	Crystalline	Multi-Crystalline
Electrical	Type/Dopant	P/Boron
	Lifetime	$\geq 1 \mu\text{sec}$
	Resistivity	1.0 ~ 3.0 Ohm-cm
Geometry	Dimension	$156 \pm 0.5 \times 156 \pm 0.5\text{mm}$
	Rectangular Angle	$90 \pm 0.3^\circ$
	Bevel Edge Length	0.5 ~ 2 mm
	Bevel Edge Angle	$45 \pm 10^\circ$
	Thickness	$200 \pm 20 \mu\text{m}$
	TTV	$\leq 30 \mu\text{m}$
Appearance	Edge Defect	No V-type sharp chip
		Q'ty of Rounded chips ≤ 1
		Depth $\leq 0.5\text{mm}$, Length $\leq 0.5\text{mm}$
	Saw Mark	$R_t \leq 15\mu\text{m}$
	Bow	$\leq 50 \mu\text{m}$
Chemical	Wafer Surface	No cracks and pin holes
	Carbon Conc.	$1.0\text{e}18 \text{ atoms/cm}^3$
	Oxygen Conc.	$8.0\text{e}17 \text{ atoms/cm}^3$

★ The Cell Efficiency Depends On Process Capability Of Cell Maker.